

IN THE CLAIMS:

Claims 1-29 have been amended herein. All of the pending claims 1 through 29 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method for forming a protective layer on a plurality of semiconductor device components, comprising:  
providing a fabrication substrate carrying a plurality of semiconductor device components, adjacent semiconductor device components on ~~said~~ the fabrication substrate being separated from one another by a street extending therebetween;  
applying a protective material to active surfaces of at least ~~said~~ the adjacent semiconductor device components;  
severing ~~said~~ the protective material and at least partially severing ~~said~~ the adjacent semiconductor device components from one another along ~~said~~ the street; and  
healing cracks and delaminated areas in ~~said~~ the protective ~~layer~~ material formed during ~~said~~ the at least partially severing.

2. (Currently Amended) The method of claim 1, wherein ~~said~~-providing comprises providing a fabrication substrate with at least one bond pad exposed at an active surface of each of ~~said~~ the adjacent semiconductor device components.

3. (Currently Amended) The method of claim 2, wherein ~~said~~-providing comprises providing a fabrication substrate with a plurality of semiconductor device components comprising at least one of semiconductor devices, interposers, and carrier substrates.

4. (Currently Amended) The method of claim 2, wherein ~~said~~-applying comprises applying ~~said~~ the protective material such that ~~said~~ the at least one bond pad of each of ~~said~~ the

plurality of semiconductor device components is exposed through ~~said~~ the protective material sufficiently to effect electrical contact therewith.

5. (Currently Amended) The method of claim 2, wherein ~~said~~-providing comprises providing ~~said~~ the fabrication substrate with each of ~~said~~ the plurality of semiconductor device components having a conductive structure protruding from ~~said~~ the at least one bond pad thereof.

6. (Currently Amended) The method of claim 5, wherein ~~said~~-applying comprises applying ~~said~~ the protective material such that ~~said~~ the protective material contacts a base portion of at least one ~~said~~ conductive structure.

7. (Currently Amended) The method of claim 6, wherein ~~said~~-applying comprises forming a support structure around ~~said~~ the base portion of ~~said~~ the at least one conductive structure.

8. (Currently Amended) The method of claim 5, wherein ~~said~~-applying comprises applying ~~said~~ the protective material such that ~~said~~ the protective material is spaced apart from a base portion of at least one ~~said~~ conductive structure.

9. (Currently Amended) The method of claim 1, wherein ~~said~~-applying comprises applying a preformed sheet of protective material to ~~said~~ the active surfaces.

10. (Currently Amended) The method of claim 9, wherein ~~said~~-applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising partially cured protective material.

11. (Currently Amended) The method of claim 9, wherein ~~said~~-applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising thermoplastic material.

12. (Currently Amended) The method of claim 9, wherein ~~said~~-applying-~~said~~ preformed sheet comprises applying a preformed sheet including apertures positioned to align with-~~said~~ the at least one bond pad of each of-~~said~~ the adjacent semiconductor device components.

13. (Currently Amended) The method of claim 2, wherein ~~said~~-applying comprises applying a preformed sheet of protective material to-~~said~~ the active surfaces.

14. (Currently Amended) The method of claim 13, wherein ~~said~~-applying-~~said~~ the preformed sheet comprises applying a preformed sheet comprising partially cured protective material.

15. (Currently Amended) The method of claim 13, wherein ~~said~~-applying-~~said~~ the preformed sheet comprises applying a preformed sheet comprising thermoplastic material.

16. (Currently Amended) The method of claim 13, wherein ~~said~~-applying-~~said~~ the preformed sheet comprises applying a preformed sheet including apertures therein positioned to align with-~~said~~ the at least one bond pad of each of-~~said~~ the adjacent semiconductor device components.

17. (Currently Amended) The method of claim 13, wherein ~~said~~-applying-~~said~~ the preformed sheet comprises applying-~~said~~ the preformed sheet such that-~~said~~ a conductive structure protruding from each of-~~said~~ the adjacent semiconductor device components on-~~said~~ the fabrication substrate-~~pass~~ passes through a plane of-~~said~~ the preformed sheet.

18. (Currently Amended) The method of claim 17, further comprising heating each ~~said~~-conductive structure prior to applying-~~said~~ the preformed sheet.

19. (Currently Amended) The method of claim 1, wherein ~~said~~-applying comprises applying-~~said~~ the protective material in a liquid state.
20. (Currently Amended) The method of claim 19, further comprising spreading-~~said~~ the protective material to form a protective layer on-~~said~~ the active surfaces.
21. (Currently Amended) The method of claim 20, wherein ~~said~~-applying-~~said~~ the protective material in-~~said~~ the liquid state comprises applying a quantity of a substantially uncured polymer to-~~said~~ the active surfaces.
22. (Currently Amended) The method of claim 21, further comprising partially curing ~~said~~ the polymer prior to ~~said~~-severing and-~~said~~ at least partially severing.
23. (Currently Amended) The method of claim 22, wherein ~~said~~-healing is effected while-~~said~~ the polymer remains in a partially cured state.
24. (Currently Amended) The method of claim 23, further comprising further curing ~~said~~ the polymer following ~~said~~-healing.
25. (Currently Amended) The method of claim 24, further comprising completely severing-~~said~~ the adjacent semiconductor device components from one another along-~~said~~ the street following ~~said~~-healing.
26. (Currently Amended) The method of claim 20, wherein ~~said~~-applying-~~said~~ the protective material in-~~said~~ the liquid state comprises applying liquefied thermoplastic material to ~~said~~ the active surfaces.

27. (Currently Amended) The method of claim 26, further comprising permitting or causing-~~said~~ the thermoplastic material to at least partially harden prior to ~~said~~-severing and-~~said~~ at least partially severing.

28. (Currently Amended) The method of claim 26, wherein ~~said~~-healing comprises heating at least portions of-~~said~~ the thermoplastic material located over peripheral regions of-~~said~~ the adjacent semiconductor device components following ~~said~~-severing and-~~said~~ at least partially severing.

29. (Currently Amended) The method of claim 27, further comprising completely severing-~~said~~ the adjacent semiconductor device components from one another along-~~said~~ the street following ~~said~~-healing.